HS1DFSH – HS1MFSH
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Taiwan Semiconductor

# 1A, 200V - 1000V High Efficient Surface Mount Rectifier

#### FEATURES

- AEC-Q101 qualified
- Glass passivated chip junction
- Ideal for automated placement
- Low power loss, high efficiency
- Fast switching for high efficiency
- Low profile package
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

## APPLICATIONS

- Freewheeling
- Snubber
- DC/DC converters
- Automotive application

## MECHANICAL DATA

- Case: SOD-128
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: Indicated by cathode band
- Weight: 0.028g (approximately)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)								
PARAMETER		SYMBOL	HS1D	HS1G	HS1J	HS1K	HS1M	UNIT
PARAIVIE I ER		STMBUL	FSH	FSH	FSH	FSH	FSH	UNIT
Marking code on the device			HS1DFH	HS1GFH	HS1JFH	HS1KFH	HS1MFH	
Repetitive peak reverse voltage		V <sub>RRM</sub>	200	400	600	800	1000	V
Reverse voltage, total rms value		V <sub>R(RMS)</sub>	140	280	420	560	700	V
Forward current		I <sub>F</sub>			1			А
Surge peak forward current, single half sine-wave	t = 8.3ms				35			А
superimposed on rated load	t = 1.0ms	I <sub>FSM</sub>			90			А
Junction temperature		TJ	-55 to +150			°C		
Storage temperature		T <sub>STG</sub>	-55 to +150			°C		

1

**KEY PARAMETERS** PARAMETER VALUE UNIT  $I_{F}$ 1 А  $V_{\text{RRM}}$ 200 - 1000 V I<sub>FSM</sub> 35 A °C 150 T<sub>J MAX</sub> Package SOD-128 Configuration Single die







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THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ТҮР	UNIT	
Junction-to-lead thermal resistance	R <sub>eJL</sub>	29	°C/W	
Junction-to-ambient thermal resistance	R <sub>eja</sub>	51	°C/W	
Junction-to-case thermal resistance	R <sub>eJC</sub>	22	°C/W	

**Thermal Performance Note:** Units mounted on PCB (5mm x 5mm Cu pad test board)

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
		$I_F = 0.5A, T_J = 25^{\circ}C$		0.80	-	V
	HS1DFSH	$I_F = 1.0A, T_J = 25^{\circ}C$		0.85	1.00	V
		$I_F = 0.5A, T_J = 125^{\circ}C$		0.65	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		0.71	0.80	V
		$I_F = 0.5A, T_J = 25^{\circ}C$		0.84	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		0.91	1.30	V
	HS1GFSH	$I_F = 0.5A, T_J = 125^{\circ}C$	V <sub>F</sub>	0.68	-	V
<b>–</b> , , (1)		$I_F = 1.0A, T_J = 125^{\circ}C$		0.76	0.86	V
Forward voltage <sup>(1)</sup>		$I_F = 0.5A, T_J = 25^{\circ}C$		0.92	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		1.02	1.70	V
	HS1JFSH	$I_F = 0.5A, T_J = 125^{\circ}C$		0.73	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		0.83	1.02	V
	HS1KFSH HS1MFSH	$I_F = 0.5A, T_J = 25^{\circ}C$		1.32	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		1.49	1.70	V
		$I_F = 0.5A, T_J = 125^{\circ}C$		0.98	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		1.16	1.39	V
Reverse current @ rated V <sub>R</sub> <sup>(2)</sup>		$T_J = 25^{\circ}C$	- I <sub>R</sub>	-	1	μA
		T <sub>J</sub> = 125°C		-	35	μA
	HS1DFSH HS1GFSH		t <sub>rr</sub>	-	50	ns
Reverse recovery time	HS1JFSH HS1KFSH HS1MFSH	I <sub>F</sub> = 0.5A, I <sub>R</sub> = 1.0A, I <sub>rr</sub> = 0.25A		-	75	ns
	HS1DFSH		CJ	20	-	pF
	HS1GFSH			17	-	pF
Junction capacitance	HS1JFSH	1MHz, V <sub>R</sub> = 4.0V		13	-	pF
	HS1KFSH HS1MFSH	1		8	-	pF

#### Notes:

(1) Pulse test with PW = 0.3ms

(2) Pulse test with PW = 30ms



# ORDERING INFORMATION

ORDERING CODE <sup>(1)</sup>	PACKAGE	PACKING
HS1xFSH	SOD-128	14,000 / Tape & Reel

Notes:

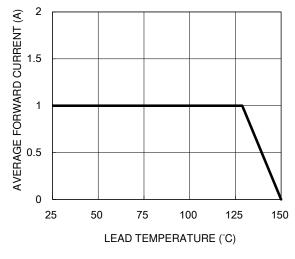
(1) "x" defines voltage from 200V(HS1DFSH) to 1000V(HS1MFSH)



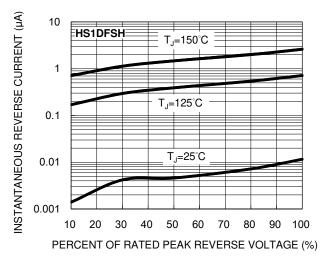
#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

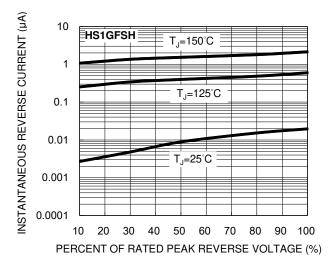
#### Fig.1 Forward Current Derating Curve



**Fig.3 Typical Reverse Characteristics** 



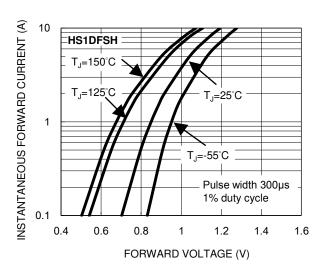




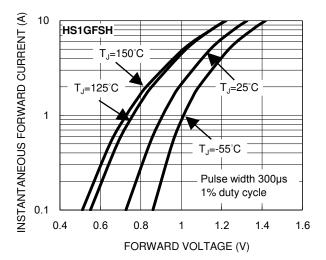
1000 HS1DFSH HS1GFSH HS1JFSH HS1KSH to HS1MFSH 100 10 f=1.0MHz Vsig=50mVp-p 1 10 REVERSE VOLTAGE (V)

#### Fig.2 Typical Junction Capacitance

**Fig.4 Typical Forward Characteristics** 



**Fig.6 Typical Forward Characteristics** 

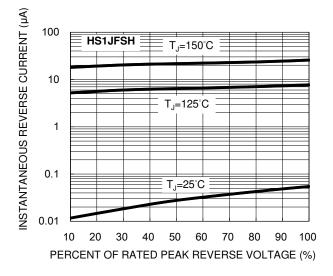




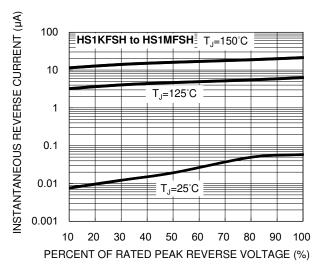
## **CHARACTERISTICS CURVES**

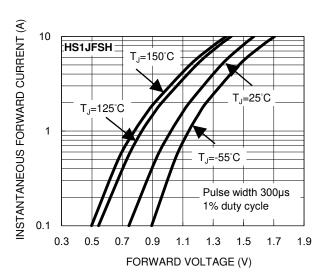
(T<sub>A</sub> = 25°C unless otherwise noted)

#### **Fig.7 Typical Reverse Characteristics**

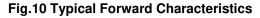


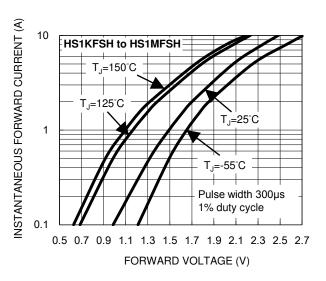


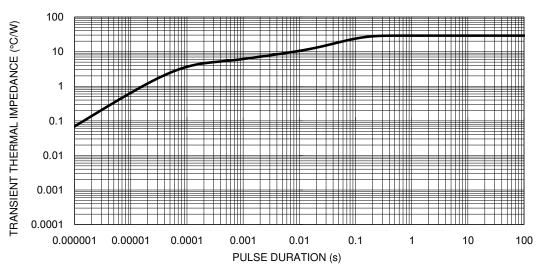




#### Fig.8 Typical Forward Characteristics







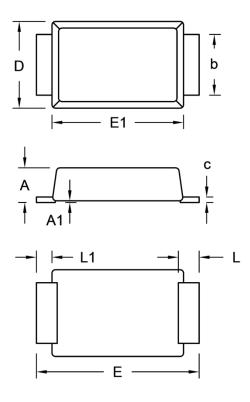
#### Fig.11 Typical Transient Thermal Impedance



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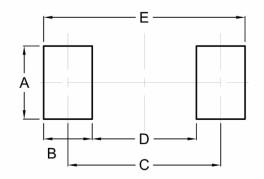
## **PACKAGE OUTLINE DIMENSIONS**

SOD-128



DIM.	Unit	(mm)	Unit	inch)	
	Min.	Max.	Min.	Max.	
A	0.90	1.10	0.035	0.043	
A1	0.00	0.10	0.000	0.004	
b	1.60	1.90	0.063	0.075	
с	0.10	0.22	0.004	0.009	
D	2.30	2.70	0.091	0.106	
E	4.40	5.00	0.173	0.197	
E1	3.60	4.00	0.142	0.157	
L	0.40	0.80	0.016	0.031	
L1	0.30	0.60	0.012	0.024	

## SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	2.10	0.083
В	1.40	0.055
С	4.40	0.173
D	3.00	0.118
E	5.80	0.228

# **MARKING DIAGRAM**



P/N	= Marking Code
YW	= Date Code
F	= Factory Code



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